This GIDEP PCN is to announce specifications change with the datasheet parameters for the following International Rectifier Part No. Note that this change is related to part specification only, and not due to a die physical change.

**IRHNA7160 (2N7432U)**
100V, Single N-Channel TID Hardened MOSFET in a SMD-2 package

**RADIATION CHARACTERISTICS CHANGE:**
Table 1 Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation

- **RDS(on) Static Drain-to-Source On-State Resistance (TO-3)**
  - For 100K Rads(Si), change from 0.045 ohm to 0.040 ohm maximum
  - For 300K-1000K Rads(Si), change from 0.062 ohm to 0.057 ohm maximum

Reference Datasheet PD-91396